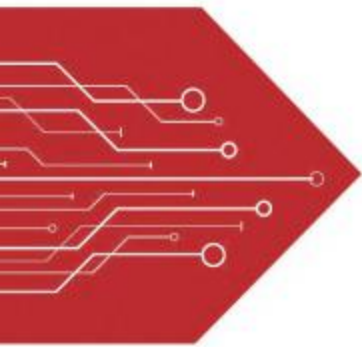


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

Product data sheet

www.msksemi.com

Description

The MSK3419DF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

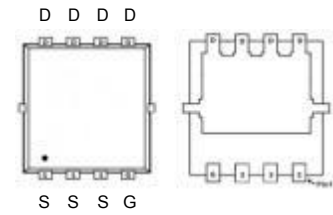
$V_{DS} = -30V, I_D = -30A$

$R_{DS(ON)} < 12m\Omega @ V_{GS} = -10V$

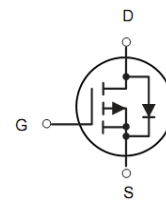
$R_{DS(ON)} < 18m\Omega @ V_{GS} = -4.5V$

Application

High side switch for full bridge converter
DC/DC converter for LCD display



DFN3X3-8L



P-Channel MOSFET

Absolute Maximum Ratings@ $T_j=25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	± 25	V
$I_D @ T_A = 25^{\circ}C$	Drain Current ³ , $V_{GS} @ 10V$	-30	A
$I_D @ T_A = 70^{\circ}C$	Drain Current ³ , $V_{GS} @ 10V$	-9.8	A
IDM	Pulsed Drain Current ¹	-65	A
$P_D @ T_A = 25^{\circ}C$	Total Power Dissipation	3.57	W
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
R_{thj-c}	Maximum Thermal Resistance, Junction-case	6	$^{\circ}C/W$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	35	$^{\circ}C/W$

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-15A	-	10	12	mΩ
		V _{GS} =-4.5V, I _D =-10A	-	14	18	mΩ
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	1.95	-2.5	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-6A	-	19	-	S
IDSS	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-30	uA
IGSS	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-15A	-	12.5	24	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	5.4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	5	-	nC
td(on)	Turn-on Delay Time	V _{DS} =-15V	-	4.4	-	ns
t _r	Rise Time	I _D =-15A	-	11.2	-	ns
td(off)	Turn-off Delay Time	R _G =3.3Ω	-	34	-	ns
t _f	Fall Time	V _{GS} =-10V	-	18	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1345	2000	pF
C _{oss}	Output Capacitance	V _{DS} =-15V f=1.0MHz	-	194	-	pF
C _{rss}	Reverse Transfer Capacitance		-	158	-	pF
t _{rr}	Reverse Recovery Time	I _S =-15A, V _{GS} =0V, dI/dt=100A/μs	-	12.4	-	ns
Q _{rr}	Reverse Recovery Charge		-	5	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

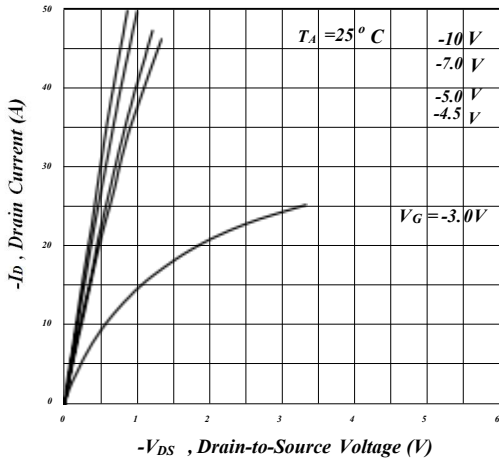


Fig 1. Typical Output Characteristics

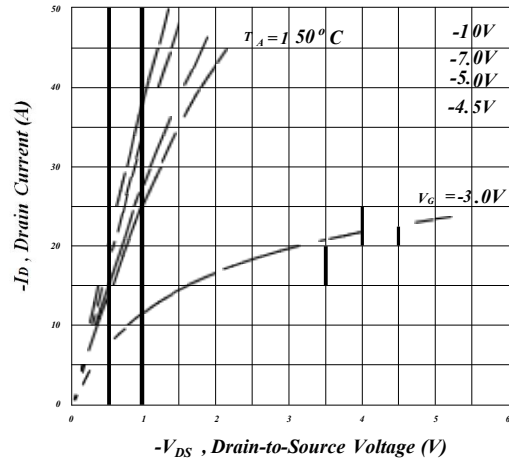


Fig 2. Typical Output Characteristics

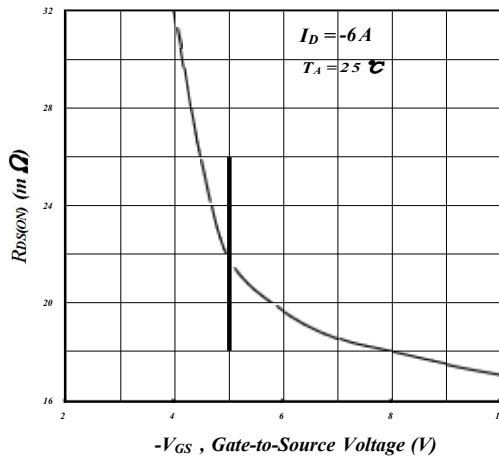


Fig 3. On-Resistance v.s. Gate Voltage

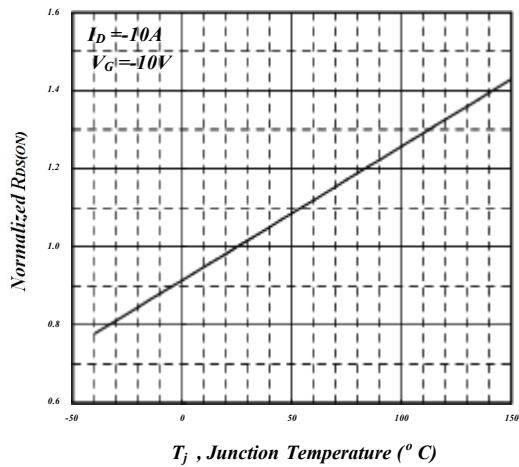


Fig 4. Normalized On-Resistance v.s. Junction Temperature

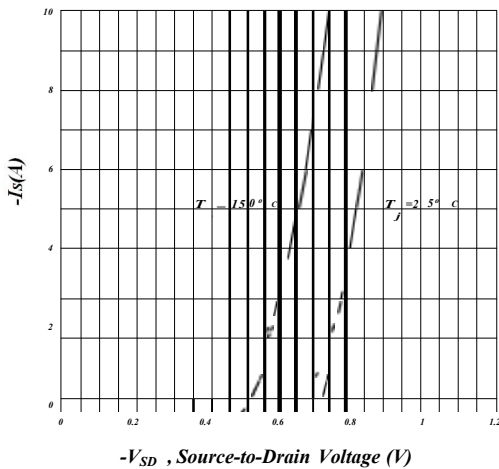


Fig 5. Forward Characteristic of Reverse Diode

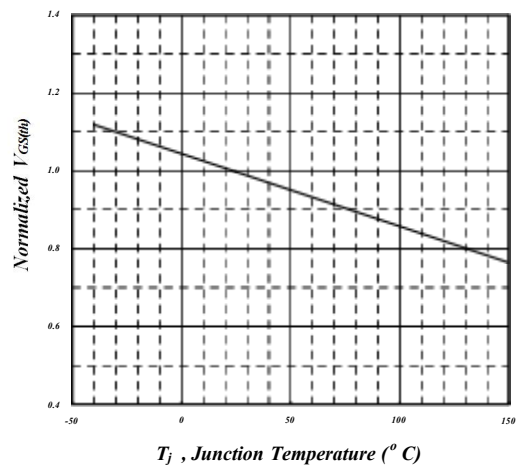


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

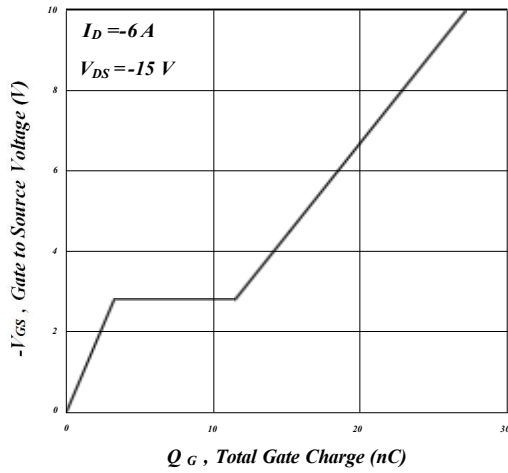


Fig 7. Gate Charge Characteristics

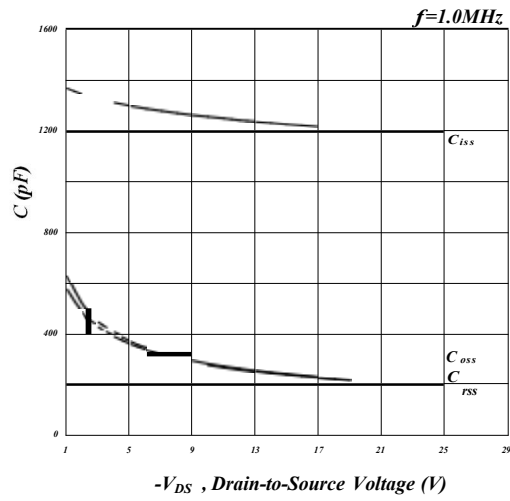


Fig 8. Typical Capacitance Characteristics

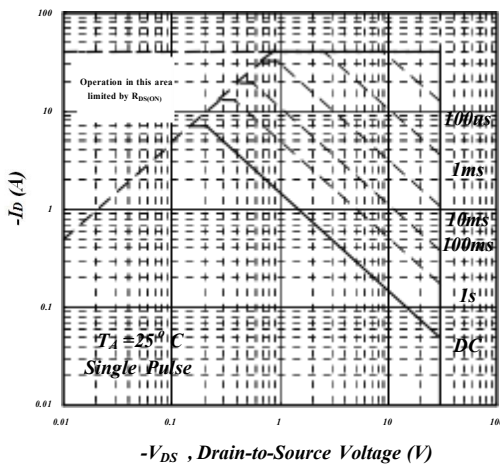


Fig 9. Maximum Safe Operating Area

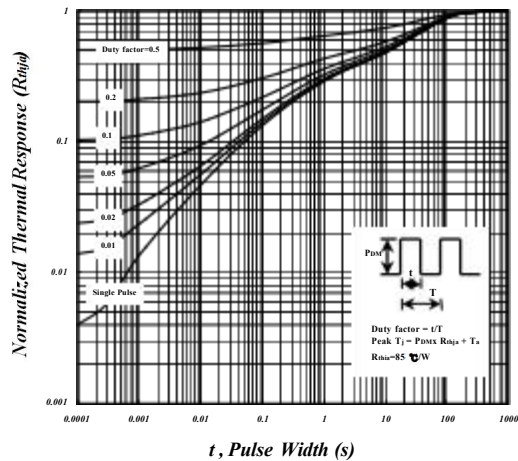


Fig 10. Effective Transient Thermal Impedance

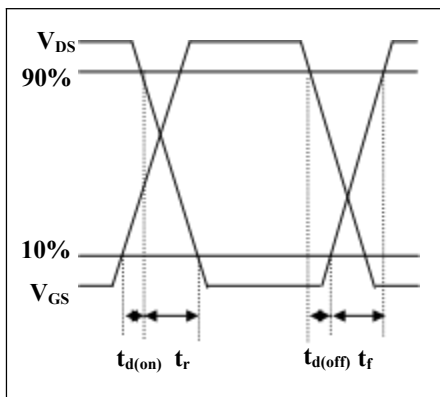


Fig 11. Switching Time Waveform

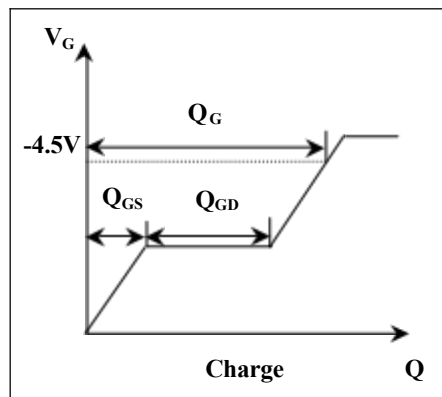
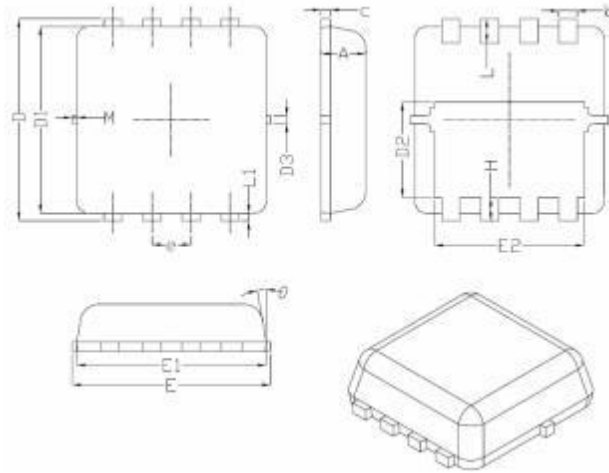


Fig 12. Gate Charge Waveform

DFN3X3-8L Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REEL SPECIFICATION

P/N	PKG	QTY
MSK3419DF	DFN3X3-8L	5000

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